MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK5A60W

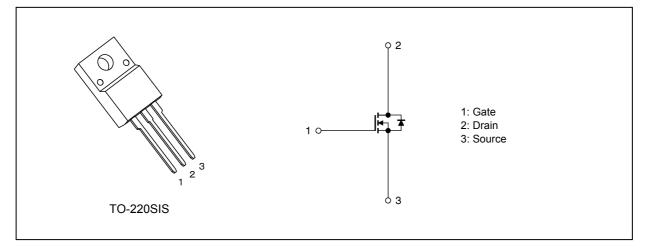
1. Applications

Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.77 \Omega$ (typ.) by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: V_{th} = 2.7 to 3.7 V (V_{DS} = 10 V, I_D = 0.27 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	600	V
Gate-source voltage		V _{GSS}	±30	
Drain current (DC)	(Note 1)	Ι _D	5.4	Α
Drain current (pulsed)	(Note 1)	I _{DP}	21.6	
Power dissipation $(T_c = 25^{\circ}C)$		PD	30	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	71	mJ
Avalanche current		I _{AR}	1.4	Α
Reverse drain current (DC)	(Note 1)	I _{DR}	5.4	
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	21.6	
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	
Isolation voltage (RMS) (t = 1.0 s)		V _{ISO(RMS)}	2000	V
Mounting torque		TOR	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	4.17	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	62.5	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_DD = 90 V, T_ch = 25°C (initial), L = 63.1 mH, R_G = 25 Ω , I_AR = 1.4 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

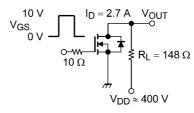
6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	600	_	—	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.27 mA	2.7	—	3.7	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 2.7 A		0.77	0.9	Ω

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V_{DS} = 300 V, V_{GS} = 0 V, f = 1 MHz	_	380	_	pF
Reverse transfer capacitance	C _{rss}			1.5	_	
Output capacitance	C _{oss}			10	_	
Effective output capacitance	C _{o(er)}	V_{DS} = 0 to 400 V, V_{GS} = 0 V		17	_	
Gate resistance	rg	V _{DS} = OPEN, f = 1 MHz		8.2	_	Ω
Switching time (rise time)	tr	See Figure 6.2.1		18	_	ns
Switching time (turn-on time)	t _{on}]		40	_	
Switching time (fall time)	t _f]		7	_	
Switching time (turn-off time)	t _{off}]		50		
MOSFET dv/dt ruggedness	dv/dt	V _{DD} = 0 to 400 V, I _D = 2.7 A	25	_	_	V/ns



Duty \leq 1%, $t_W =$ 10 μs

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, V_{GS} \text{ = } 10 \text{V}, \text{I}_{D} \text{ = } 5.4 \text{A}$	—	10.5	_	nC
Gate-source charge 1	Q _{gs1}			2.7	_	
Gate-drain charge	Q _{gd}			5.8	_	

6.4. Source-Drain Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 5.4 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 2.7 A, V _{GS} = 0 V	_	200	_	ns
Reverse recovery charge	Q _{rr}	-dI _{DR} /dt = 100 A/μs	_	1.3	_	μC
Peak reverse recovery current	I _{rr}		_	13	_	А
Diode dv/dt ruggedness	dv/dt	I_{DR} = 2.7 A, V_{GS} = 0 V, V_{DD} = 400 V	15	_	_	V/ns

7. Marking (Note)

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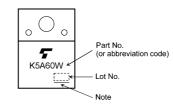
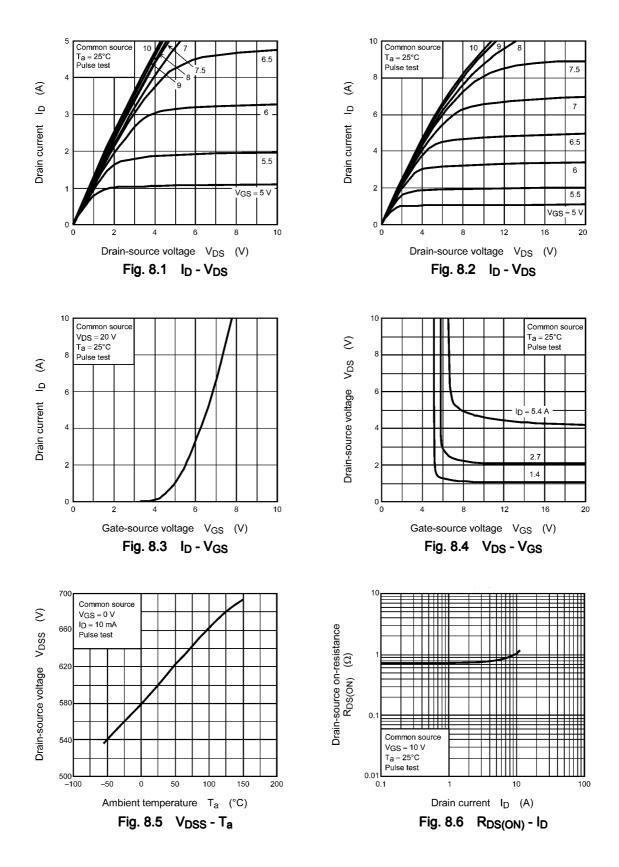


Fig. 7.1 Marking

 Note: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]
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8. Characteristics Curves (Note)



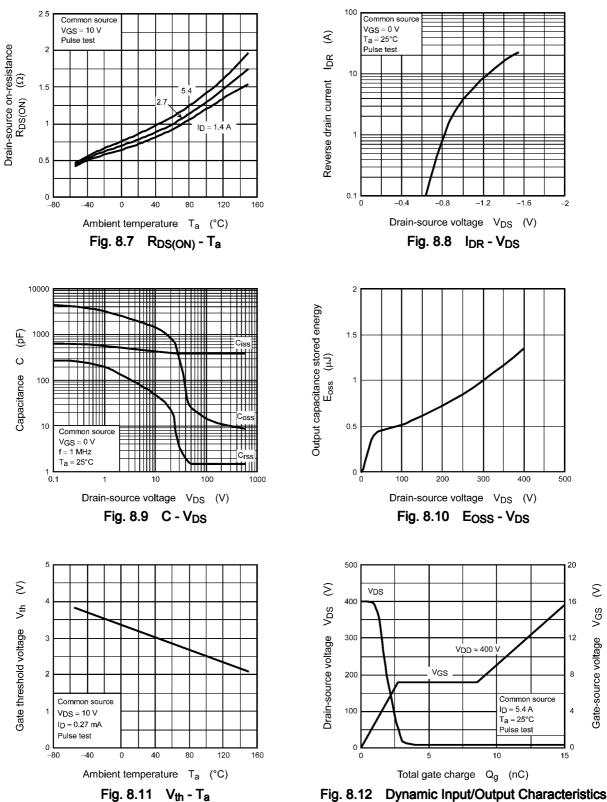


Fig. 8.12 Dynamic Input/Output Characteristics

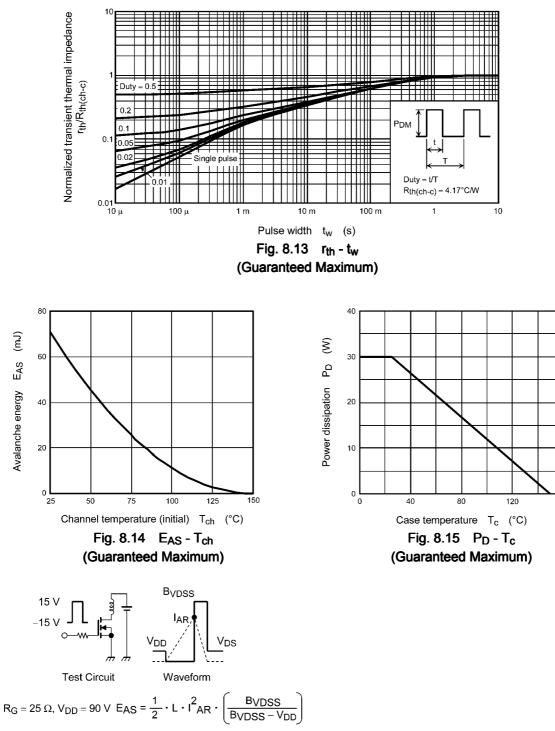
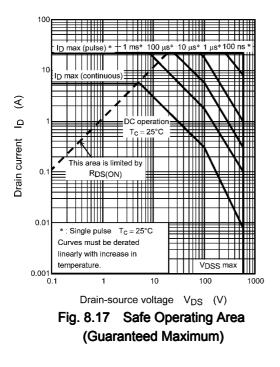


Fig. 8.16 Test Circuit/Waveform

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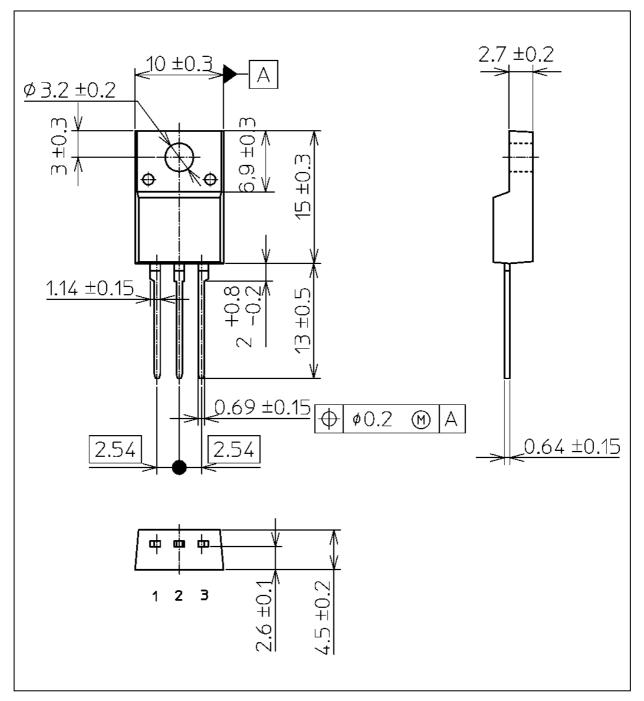


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

TK5A60W

Unit: mm



Weight: 1.7 g (typ.)

	Package Name(s)
JEITA: SC-67	
TOSHIBA: 2-10U1S	
Nickname: TO-220SIS	

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